



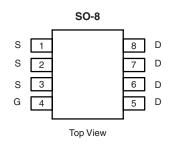
N-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
20	0.009 at V _{GS} = 4.5 V	13.5		
	0.013 at V _{GS} = 2.5 V	11		

FEATURES

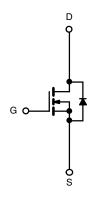
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4466DY-T1-E3 (Lead (Pb)-free)

Si4466DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Comment /T 150 °C)	T _A = 25 °C	- I _D	13.5	9.5	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		10.5	7.5	
Pulsed Drain Current		I _{DM}	50		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.7	1.36	
M	T _A = 25 °C	P _D	3.0	1.5	w
Maximum Power Dissipation ^a	T _A = 70 °C		1.9	0.95	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestor Localitan to Applicant	t ≤ 10 s	- R _{thJA}	33	42	°C/W
Maximum Junction-to-Ambient ^a	Steady State		70	84	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

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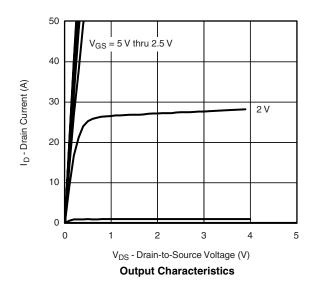
MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	1.0	1.4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zava Cata Valtaga Dvain Curvent		V _{DS} = 20 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
	В	$V_{GS} = 4.5 \text{ V}, I_D = 13.5 \text{ A}$	0.0055 0.00		0.009	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 11 A		0.0078	0.013		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 13.5 A		70		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.70	1.1	V	
Dynamic ^b							
Gate Charge	Q_g			40	60		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 13.5 \text{ A}$		7		nC	
Gate-Drain Charge	Q_{gd}			12			
Gate Resistance	R_g		0.5	1.9	3.3	Ω	
Turn-On Delay Time	t _{d(on)}			20	30		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		15	25		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		150	250	ns	
Fall Time	t _f			70	110		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		55	90		

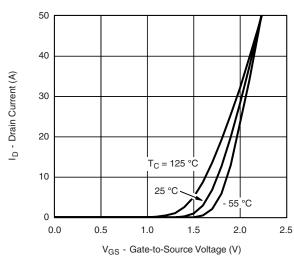
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



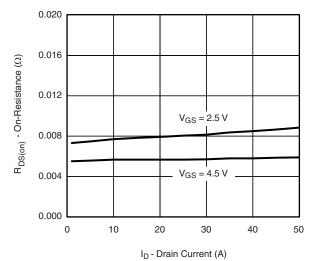




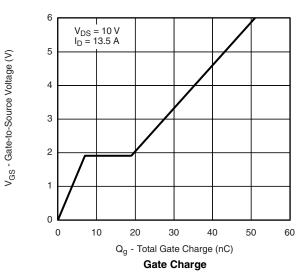


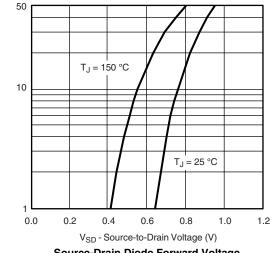


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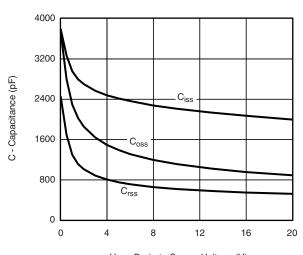


On-Resistance vs. Drain Current



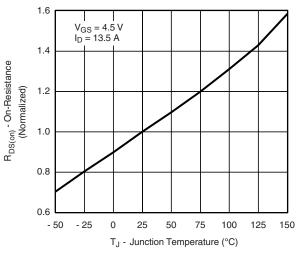


Source-Drain Diode Forward Voltage

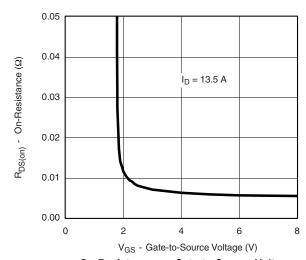


V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



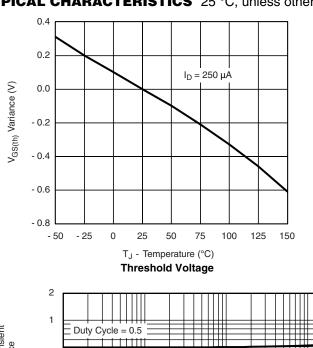
On-Resistance vs. Gate-to-Source Voltage

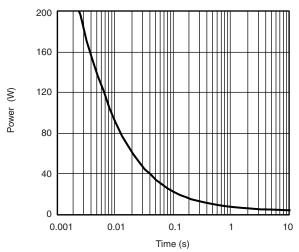
Is - Source Current (A)

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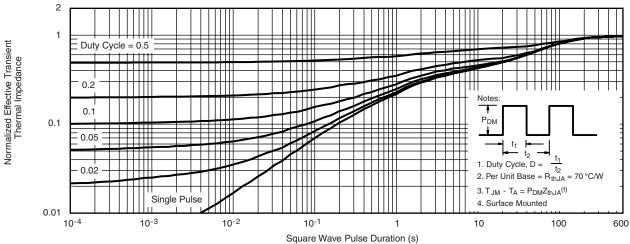
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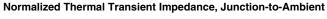
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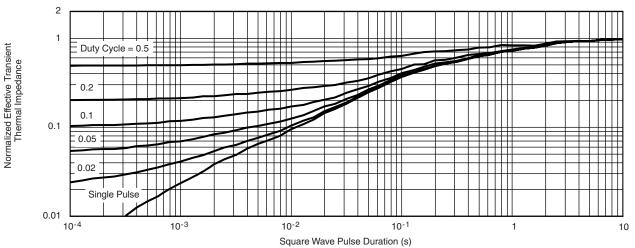




Single Pulse Power, Junction-to-Ambient







Normalized Thermal Transient Impedance, Junction-to-Foot

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